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ABSTRACT OF THE DISCLOSURE

The present invention is a method of measuring capacitance of micro structures in an integrated circuit wherein the micro structure includes a first terminal and a second terminal separated by an insulator and at least a third terminal separated from the first terminal by an insulator. The method comprises applying biasing voltage to the second terminal and applying the same potential to the first and third terminals. An electrical characteristic between the first and second terminals are measured to determine the capacitance between the first and second terminals.

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